

Daisuke Nakamura

List of Publications by Citations

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32
papers

735
citations

10
h-index

27
g-index

36
ext. papers

833
ext. citations

4.2
avg, IF

4.11
L-index

#	Paper	IF	Citations
32	Ultra-high-quality silicon carbide single crystals. <i>Nature</i> , 2004 , 430, 1009-12	50.4	307
31	Investigation of carrier lifetime in 4H-SiC epilayers and lifetime control by electron irradiation. <i>Applied Physics Letters</i> , 2007 , 90, 202109	3.4	158
30	Topographic study of dislocation structure in hexagonal SiC single crystals with low dislocation density. <i>Journal of Crystal Growth</i> , 2007 , 304, 57-63	1.6	35
29	Liquid-Phase Exfoliation of Germanane Based on Hansen Solubility Parameters. <i>Chemistry of Materials</i> , 2018 , 30, 5333-5338	9.6	23
28	Sintered tantalum carbide coatings on graphite substrates: Highly reliable protective coatings for bulk and epitaxial growth. <i>Applied Physics Letters</i> , 2015 , 106, 082108	3.4	22
27	Tantalum carbide coating via wet powder process: From slurry design to practical process tests. <i>Journal of the European Ceramic Society</i> , 2017 , 37, 1175-1185	6	18
26	Simple and quick enhancement of SiC bulk crystal growth using a newly developed crucible material. <i>Applied Physics Express</i> , 2016 , 9, 055507	2.4	14
25	TaC-coated graphite prepared via a wet ceramic process: Application to CVD susceptors for epitaxial growth of wide-bandgap semiconductors. <i>Journal of Crystal Growth</i> , 2017 , 478, 163-173	1.6	12
24	Nanopipe formation as a result of boron impurity segregation in gallium nitride grown by halogen-free vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2016 , 120, 245703	2.5	12
23	Nontoxic organic solvents identified using an a priori approach with Hansen solubility parameters. <i>Chemical Communications</i> , 2017 , 53, 4096-4099	5.8	10
22	Macro-defect-free homoepitaxial GaN growth through halogen-free vapor-phase epitaxy on native GaN seeds. <i>Journal of Crystal Growth</i> , 2018 , 494, 17-25	1.6	10
21	Halogen-free vapor phase epitaxy for high-rate growth of GaN bulk crystals. <i>Applied Physics Express</i> , 2017 , 10, 045504	2.4	10
20	Direct determination of Burgers vector sense and magnitude of elementary dislocations by synchrotron white x-ray topography. <i>Journal of Applied Physics</i> , 2008 , 103, 013510	2.5	9
19	Reduction of Dislocations in the Bulk Growth of SiC Crystals. <i>Materials Science Forum</i> , 2006 , 527-529, 3-8	0.4	9
18	Local atomic arrangement of Pb and Sn on the Si(111)-(Pb,Sn) surface. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 96, 145-149	3.1	9
17	Self-recovery of monolayer Pb adsorbates on the Si(111)-1 \times 1-Pb surface under ion irradiation at room temperature. <i>Surface Science</i> , 1999 , 425, 174-179	1.8	9
16	Self-Assembled Single-Crystalline GaN Having a Bimodal Meso/Macropore Structure To Enhance Photoabsorption and Photocatalytic Reactions. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 4233-4241	9.5	9

15	Impact of SiC Structural Defects on the Degradation Phenomenon of Bipolar SiC Devices. <i>Materials Science Forum</i> , 2003 , 433-436, 917-920	0.4	8
14	Self-Healing Phenomenon of Micropipes in Silicon Carbide. <i>Materials Science Forum</i> , 2002 , 389-393, 103-106	1.4	8
13	Fabrication of large-sized TaC-coated carbon crucibles for the low-cost sublimation growth of large-diameter bulk SiC crystals. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 085504	1.4	7
12	Ultrahigh-yield growth of GaN via halogen-free vapor-phase epitaxy. <i>Applied Physics Express</i> , 2018 , 11, 065502	2.4	7
11	Significant increase in GaN growth rate by halogen-free vapor phase epitaxy with porosity-controlled evaporator. <i>Applied Physics Express</i> , 2017 , 10, 095503	2.4	6
10	Porosity-controlled multilayer TaC coatings prepared via wet powder process for multi-functional reactor components in GaN crystal growth system. <i>Ceramics International</i> , 2018 , 44, 21284-21288	5.1	5
9	Resistive heater element made of highly durable TaC-coated graphite for high-temperature and highly corrosive processes: application to MOCVD GaN epitaxial growth. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, 075509	1.4	4
8	Hansen Solubility Parameters of Stacked Silicenes Derived from Porous Silicon. <i>ACS Omega</i> , 2019 , 4, 11838-11843	3.5	4
7	Origin and effective reduction of inversion domains in aluminum nitride grown by a sublimation method. <i>Journal of Crystal Growth</i> , 2017 , 478, 33-41	1.6	3
6	Ultrahigh-quality single crystals of silicon carbide by alternate repetition of growth perpendicular to c-axis. <i>Microelectronic Engineering</i> , 2006 , 83, 139-141	2.5	2
5	Growth of high-quality GaN by halogen-free vapor phase epitaxy. <i>Applied Physics Express</i> , 2020 , 13, 085509	2.4	2
4	Transformation of hollow-core screw dislocations: transitional configuration of superscrew dislocations. <i>Japanese Journal of Applied Physics</i> , 2020 , 59, 095502	1.4	2
3	Tungsten carbide layers deposited on graphite substrates via a wet powder process as anti-parasitic-reaction coatings for reactor components in GaN growth. <i>CrystEngComm</i> , 2020 , 22, 2632-2641	3.3	1
2	Synchrotron X-ray Topographic Analysis of Dislocation Structures in Bulk SiC Single Crystal. <i>Materials Science Forum</i> , 2006 , 527-529, 407-410	0.4	
1	Mechanism and enhancement of anti-parasitic-reaction catalytic activity of tungsten-carbide-coated graphite components for the growth of bulk GaN crystals. <i>Applied Physics Express</i> , 2022 , 15, 045501	2.4	